

Four Wave Mixing Studies of Polaron Dephasing in InAs/GaAs Self-Assembled Quantum Dots

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Outline

Introduction

Strong coupling and implications for carrier relaxation

Polaron dephasing

Motivation, technique used

Results

Experimental data

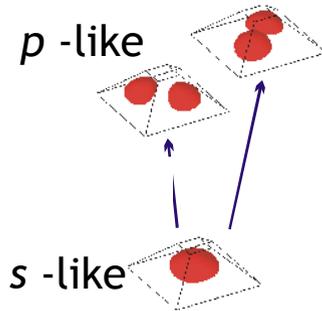
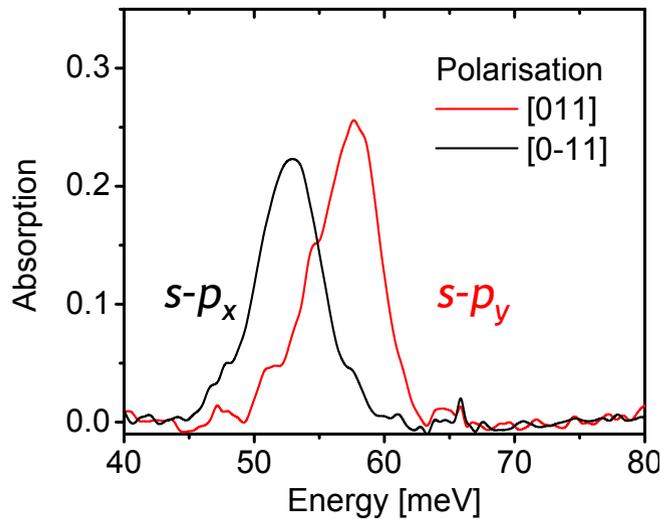
Calculation of acoustic phonon sidebands

Calculation of four-wave mixing signal: virtual and real transitions

Comparison of the theory and experiment

Summary

InAs/GaAs QDs: Intraband spectroscopy



Intraband absorption

- Normal incidence geometry - in plane dipole
- Inhomogeneous broadening: FWHM ~ 5 meV
- Polarisation dependence due to QD wf anisotropy: splitting of p -states ~ 5 meV

Studies have shown that electrons and phonons in QDs are in the strong coupling regime - forming **polarons**

See for example:

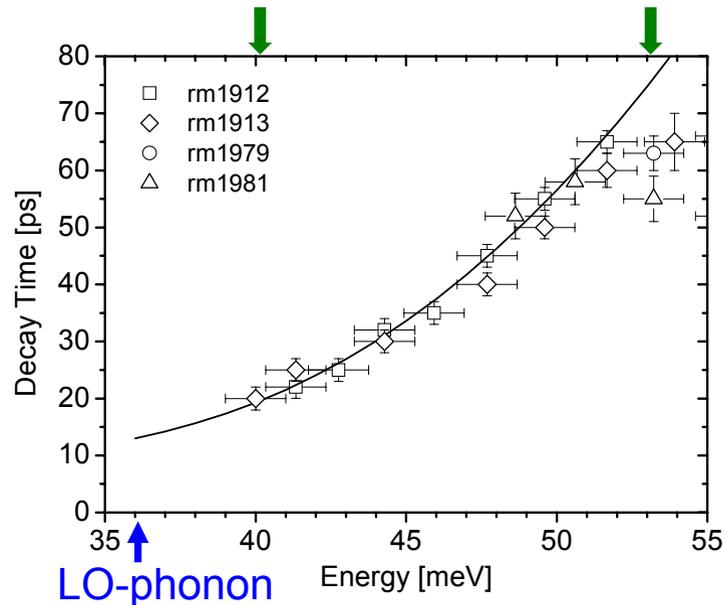
S. Hameau *et al.*, Phys. Rev. Lett. **83** 4152 (1999)

X.-Q. Li & Y. Arakawa, Phys. Rev. B **57** 12285 (1998)

Implications for carrier relaxation

- ❑ Weak coupling picture does not apply, hence ‘phonon bottleneck’ does not exist
- ❑ Excited state polarons decay due to finite lifetime of the LO phonon - as the phonon fraction of the polaron increases the polaron lifetime decreases

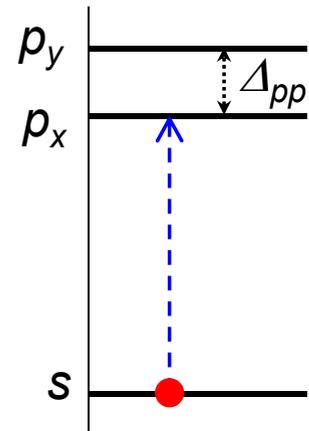
Phonon fraction $\sim 70\%$ $\sim 10\%$



X.-Q. Li & Y. Arakawa, *Phys. Rev. B* **57** 12285 (1998),
S. Sauvage *et al.*, *Phys. Rev. Lett.* **88** 177402 (2002),
E.A. Zibik *et al.*, *Phys. Rev. B* **70** 161305(R) (2004)

Polaron dephasing - motivation

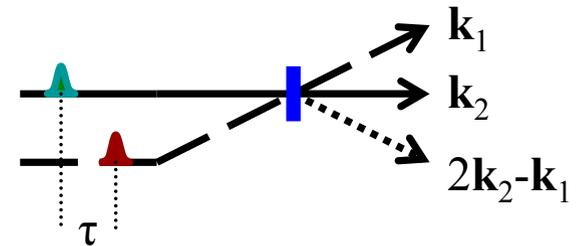
- ❑ Understanding dephasing processes due to the electron-phonon interaction in QDs is a key issue for many potential applications
- ❑ Provides homogeneous linewidth information - unlike interband case, intraband absorption measurements of single QDs not possible
- ❑ No holes present in the samples
- ❑ Simple 3-level energy structure makes easier to analyse the results and allows a clear picture of dephasing mechanisms to be obtained



Four Wave Mixing (FWM): Photon Echo

□ Highly sensitive technique for studying the coherent behaviour of carriers in quantum dot systems

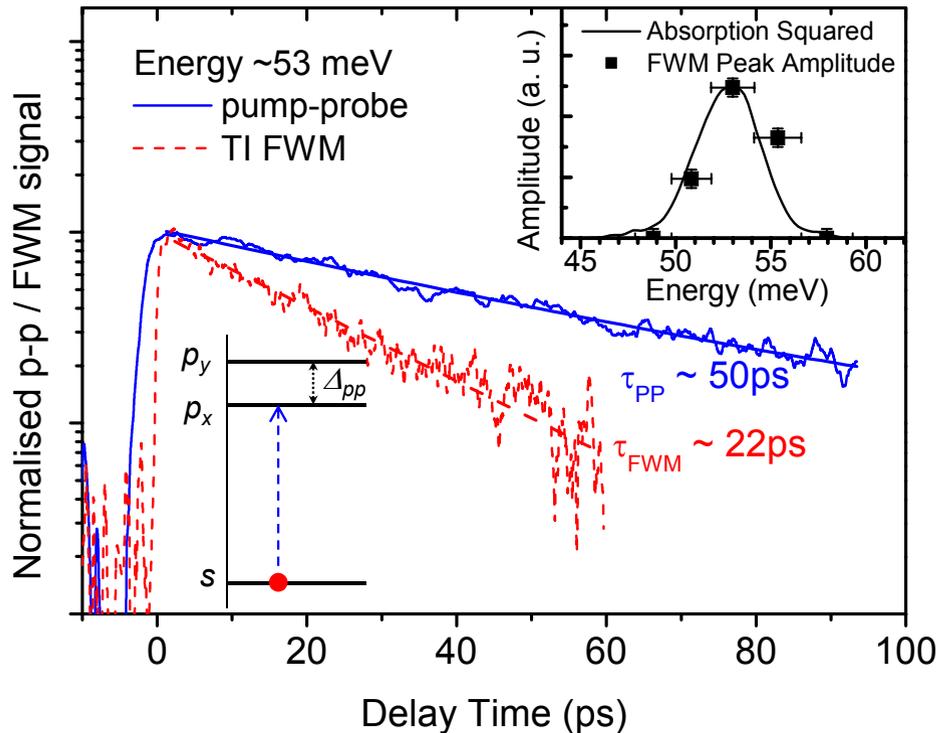
□ Incident pulses k_1 and k_2 ; Delay time τ



□ The photon echo ($2k_2 - k_1$) is measured as a function of the time delay between the incident pulses and the dephasing time is deduced from the time decay of the coherent polarisation.

□ Pulse duration ~ 1 ps

FWM comparison with Pump-Probe

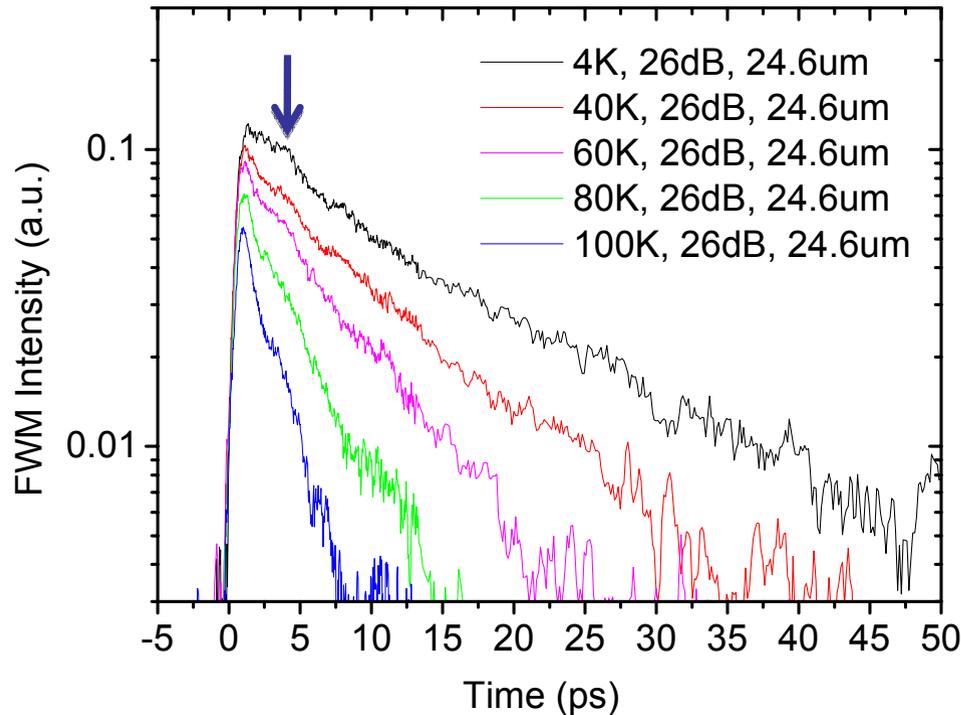


- ❑ Measurements performed in the χ^3 regime: ~250 pJ per pulse
- ❑ FWM amplitude follows dot linear absorption
- ❑ Very different decay times for pump-probe (~50ps) and FWM (~20ps)
- ❑ Inhomogeneous broadening: $T_2 = 4 \times \tau_{FWM} = 88\text{ps}$, close to $2T_1 = 100\text{ps}$

$$\frac{1}{T_2} = \frac{1}{2T_1} + \frac{1}{T_2^*}$$

- ❑ Pure dephasing time: ~500ps, hence at low temperature the dephasing is mainly determined by *population relaxation*

Polaron dephasing results



- ❑ Polaron dephasing time (T_2) decreases dramatically with increasing temperature: from ~90ps at 10K to ~15ps at 100K (*polaron lifetime* T_1 decreases from ~50ps to ~40ps)
- ❑ This corresponds to decrease of the pure dephasing time from 500ps to ~18ps over the same temperature range

Theoretical approach

- Polaron interaction with longitudinal acoustic phonons (deformation potential coupling) treated using the independent Boson model
- Deformation potential coupling matrix element

$$M_{\mathbf{q}}^{ij} = D_c \sqrt{\frac{\hbar q}{2\rho c_s V}} \langle i | e^{i\mathbf{q}\cdot\mathbf{r}} | j \rangle \quad \text{where } i = s, p_x, p_y$$

- Absorption lineshape is given by

$$A(\omega) = Z e^{f(\omega)} = Z \left\{ \delta(\omega) + f(\omega) + \frac{1}{2}[f \otimes f](\omega) + \dots + \frac{1}{p!}[f \otimes^{p-1} f](\omega) \right\}$$

Zero-phonon line 1-phonon absorption/emission

p -phonon processes

where

$$f(\omega) = \sum_{\mathbf{q}} \frac{|M_{\mathbf{q}}^{p_x p_x} - M_{\mathbf{q}}^{s s}|^2}{\omega_{\mathbf{q}}^2} [N(\omega) + \Theta(\omega)] \delta(\omega - \omega_{\mathbf{q}})$$

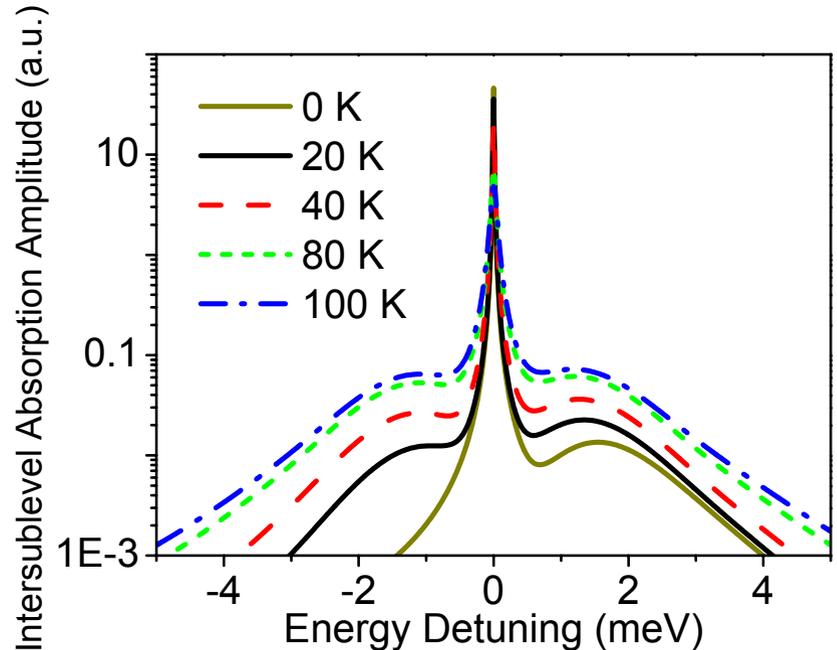
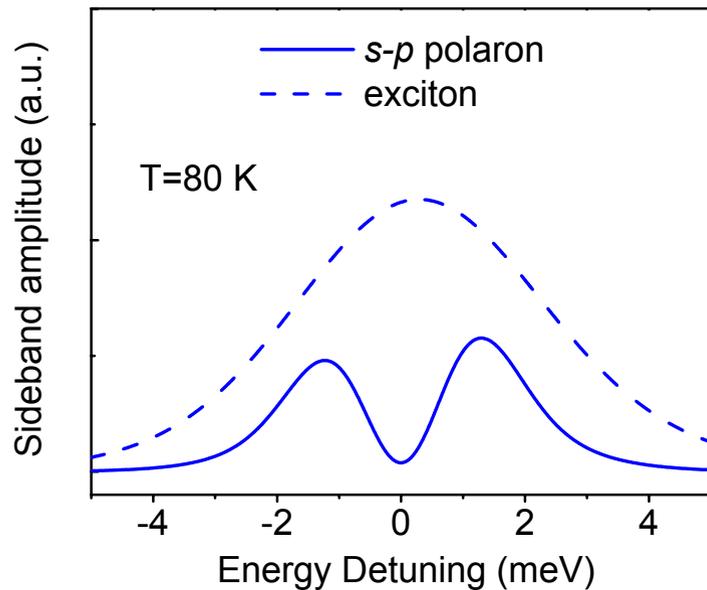
and the weight of the zero phonon line

$$Z = \exp \left[- \int_{-\infty}^{+\infty} d\omega f(\omega) \right]$$

Acoustic phonon sidebands

Interband:
$$f(\omega) = \sum_{\mathbf{q}} \frac{|M_{\mathbf{q}}^{s_e s_e} + M_{\mathbf{q}}^{s_h s_h}|^2}{\omega_{\mathbf{q}}^2} [N(\omega) + \Theta(\omega)] \delta(\omega - \omega_{\mathbf{q}})$$

$$M_{\mathbf{q}}^{s_e s_e} + M_{\mathbf{q}}^{s_h s_h} = \sqrt{\frac{\omega_{\mathbf{q}}}{2c\rho}} \left(\underset{\downarrow -7.2 \text{ eV}}{D_c \langle s_e | e^{i\mathbf{q} \cdot \mathbf{r}_e} | s_e \rangle} + \underset{\downarrow -1.3 \text{ eV}}{D_v \langle s_h | e^{i\mathbf{q} \cdot \mathbf{r}_e} | s_h \rangle} \right)$$

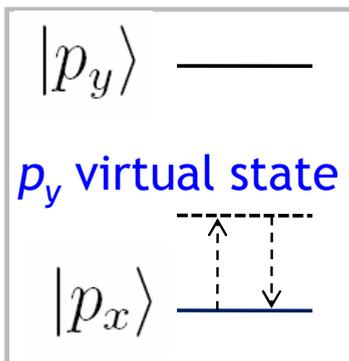


Four wave mixing – calculations

- ❑ FWM dynamics calculated for excitation in resonance with the s to p_x transition, taking into account polaron decay to the s state, real and virtual transitions to the p_y state, as well as the presence of phonon sidebands
- ❑ Broadening of the zero phonon line due to real and virtual phonon transitions from p_x to p_y

Absorption+Emission

$$\Gamma_2^* = \frac{1}{2\pi} \int_0^{+\infty} d\omega \frac{\Gamma_{pp}^2(\omega) N(\omega) [N(\omega) + 1]}{(\omega - \Delta_{pp})^2 + \left(\frac{\Gamma_{pp}(\omega) [N(\omega) + 1]}{2} \right)^2} + \frac{\Gamma_{pp}^2(\omega) N(\omega) [N(\omega) + 1]}{(\omega + \Delta_{pp})^2 + \left(\frac{\Gamma_{pp}(\omega) N(\omega)}{2} \right)^2}$$



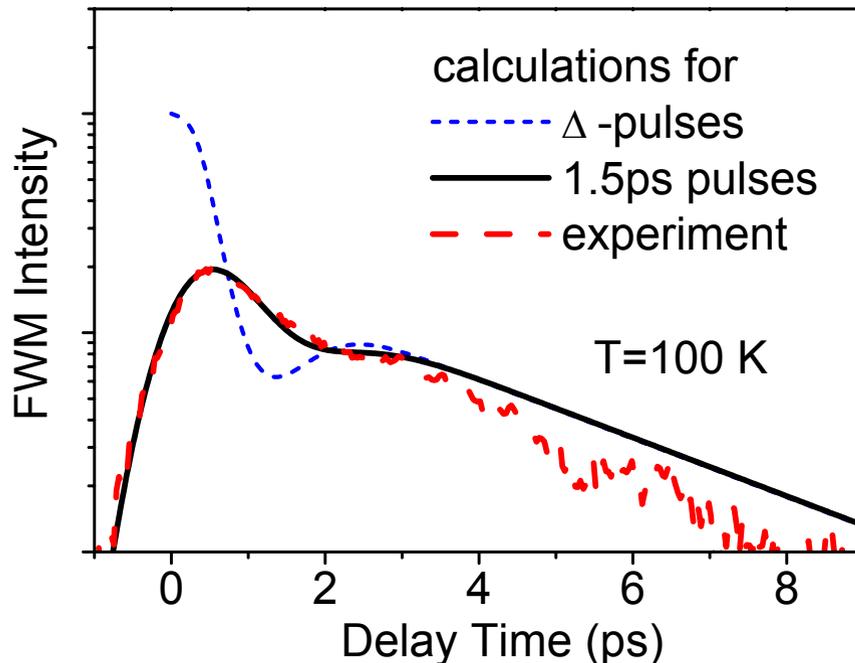
Emission+Absorption

where $\Gamma_{pp}(\varepsilon) = 2\pi \sum_{\mathbf{q}} |M_{\mathbf{q}}^{p_x p_y}|^2 \delta(\varepsilon - \hbar\omega_{\mathbf{q}})$

Four wave mixing – calculations

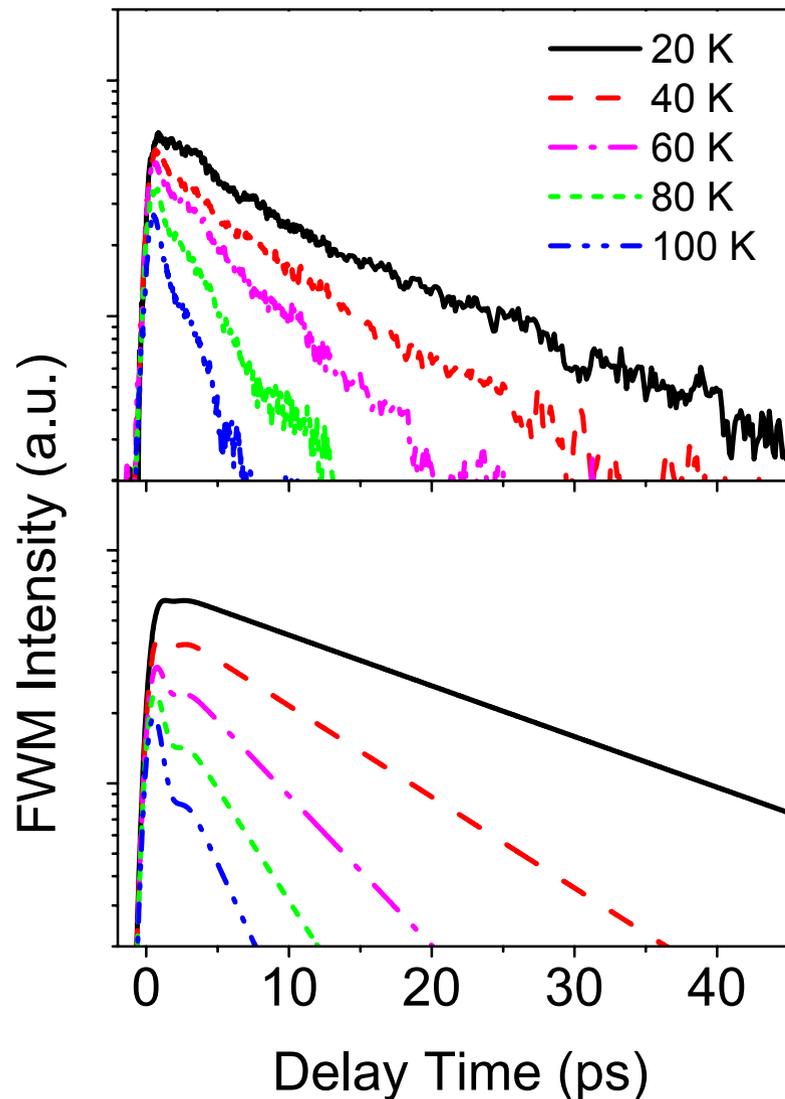
- Intensity of the FWM response to a delta pulse as a function of the delay time between the 2 pulses:

$$I(t) \propto \Theta(t) \exp \left[-2\Gamma_2 t - 16 \int_{-\infty}^{+\infty} d\varepsilon f(\varepsilon) \sin^2 \left(\frac{\varepsilon t}{2\hbar} \right) \right]$$



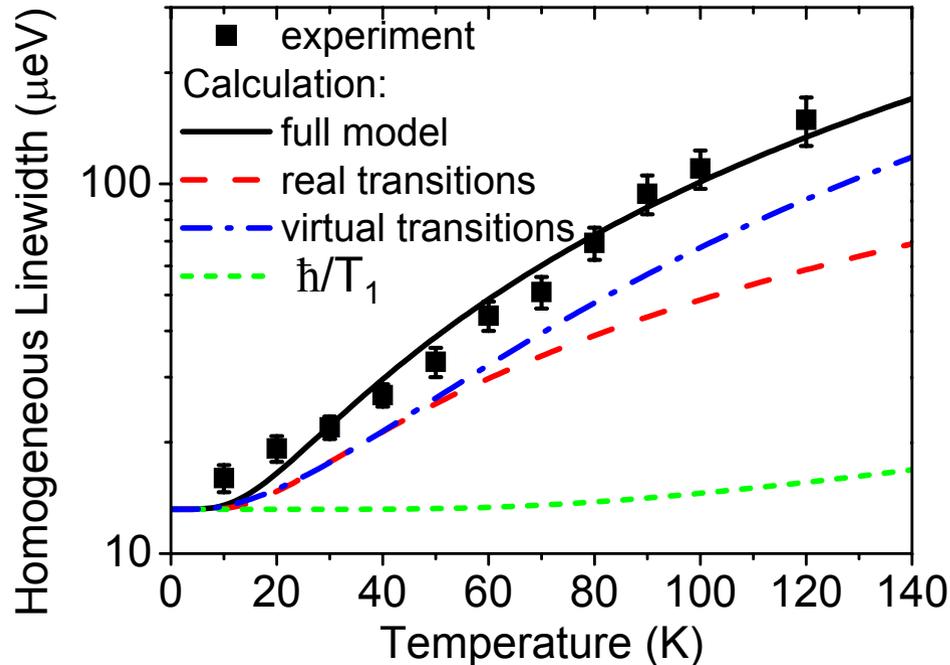
- Presence of acoustic sidebands results in oscillatory behaviour in the FWM signal shortly (< 5 ps) after resonant excitation of the lowest energy conduction band transition, which is due to coherent acoustic phonon generation

FWM – temperature dependence



- Excellent agreement found between our measured and calculated FWM dynamics

FWM – temperature dependence



- Very good agreement between calculated total linewidth ($\Gamma_2 = \Gamma_1 + \Gamma_2^*$) of the zero phonon line and values deduced from experiment
- Virtual transitions dominate dephasing at high temperature due to the quadratic dependence on phonon occupation number

Summary

- First studies of polaron dephasing processes in InAs dots using far infrared transient four wave mixing (FWM) spectroscopy
- Acoustic phonon sidebands ~ 1.5 meV apart from zero-phonon line ($\Gamma_{\text{hom}} \sim 20$ μeV)
- Oscillatory behaviour in the FWM signal shortly (< 5 ps) after resonant excitation is due to coherent acoustic phonon generation
- Subsequent single exponential decay yields long intraband dephasing times of ~ 90 ps
- Both real and virtual acoustic phonon processes are necessary to explain the temperature dependence of the polarisation decay